# SCALE Dual-Channel Plug-and-Play Driver

Driver solution for 130mm x 140mm dual IGBT modules with electrical interface for 2-level topologies

#### Abstract

The 2SB315A-2MBI800VT-170E is a dual-channel driver with an electrical interface based on CONCEPT's dual SCALE driver 2SD315AI, a proven technology for reliable driving and safe operation of IGBTs.

The driver is matched to the 1700V module 2MBI800VT-170E from Fuji. Its plug-andplay capability makes it ready to operate immediately after mounting. The user needs invest no effort in designing or adjusting it to a specific application.

For drivers adapted to other types of high-power and high-voltage IGBT modules, refer to <u>www.IGBT-Driver.com/go/plug-and-play</u>

## **Product Highlights**

- ✓ Suitable for 2MBI800VT-170E
- Plug-and-play solution
- ✓ Active clamping of V<sub>ce</sub> at turn-off
- ✓ IGBT short-circuit and overcurrent protection
- ✓ No electrolytic capacitors
- ✓ 20-pin flat cable interface
- ✓ Monitoring of power supply voltage
- ✓ Duty cycle 0... 100%
- Extremely reliable; long service life
- ✓ Shortens application development time

## **Applications**

- ✓ Inverters
- ✓ Motor drives
- 🗸 UPS
- Power-factor correctors
- ✓ Wind-power converters
- ✓ Welding
- SMPS
- and many others



#### Important: Please refer to the relevant manuals!

This data sheet contains only product-specific data. A detailed description, must-read application notes and general data applicable to this driver family are found in: "Description and Application Manual for 2SB315A SCALE Plug-and-play IGBT Driver".

See <u>www.IGBT-Driver.com/go/2SB315A</u>

#### Dimensions

Dimensions: 130 x 145 mm, 21 mm height (30 mm with connector X1 and flat cable).

Mounting principle: Connected to IGBT module with screws.

#### Absolute Maximum Ratings

Parameter	Remarks	Min	Max	Units
Supply voltage V <sub>DC</sub>	VDC to GND (Note 1)	0	16	V
Supply voltage V <sub>DD</sub>	VDD to GND	0	16	V
Logic input voltage	To GND	0	$V_{DD}$	V
Gate peak current I out	Note 6	-15	+15	А
Average supply current IDC	Notes 2,3		500	mA
Output power per gate	Note 3		3	W
Switching frequency	Note 3		8	kHz
DC-link voltage	Note 4		1200	V
Operating temperature	Note 3	-40	+85	°C
Storage temperature		-40	+90	°C

All data refer to  $+25^{\circ}$ C and  $V_{DC} = 15$ V unless otherwise specified

## **Electrical Characteristics**

Power supply	Remarks	Min	Тур.	Мах	Units
Nominal supply voltage V <sub>DC</sub>	To GND (Note 1)		15		V <sub>dc</sub>
Supply current $I_{DC}$	Without load		80		mÃ
Supply current $I_{DC}$	At 8 kHz switching frequen	су	500		mA
Efficiency η	Internal DC/DC converter		85		%
Nominal supply voltage $V_{DD}$	To GND		15		$V_{dc}$
Supply current <i>I<sub>DD</sub></i>	Without load		10		mA
Supply current <i>I<sub>DD</sub></i>	At 8 kHz switching frequen	су	12		mA
Power supply monitoring	Test conditions	Min	Тур.	Мах	Units
Turn-on threshold $V_{th}$	Note 5		10.6		V <sub>dc</sub>
Hysteresis on/off	Note 5		0.6		$V_{dc}$
Short circuit protection	Remarks	Min	Тур.	Мах	units
V <sub>ce</sub> -monitoring threshold	Betw. aux. terminals		6.3		V
Response time	Note 7		10.8		μs
Blocking time	After failure (Note 8)		1		S
Logic inputs	Test conditions	Min	Тур.	Мах	Units
Input voltage	All inputs	0		V <sub>DD</sub>	V <sub>dc</sub>
Timing characteristics	Test conditions	Min	Тур.	Мах	Units
Turn-on delay t <sub>pd(on)</sub>	Note 9		400		ns
Turn-off delay $t_{pd(off)}$	Note 9		500		ns
Output rise time <i>t<sub>r(out)</sub></i>	Gx to Ex (Note 10)		150		ns
Output fall time $t_{f(out)}$	Gx to Ex (Note 10)		80		ns
Dead time between outputs	Half-bridge mode		2.5		μs
Outputs	Test conditions	Min	Тур.	Max	Units
Turn-on gate resistor R <sub>g(on)</sub>		-	1.5		Ω
Turn-off gate resistor Rg(off)			9.1		Ω
Output current SOx		1.5			mA
Output voltage rating SOx	SOx to GND			$V_{DD}$	V

Electrical insulation	Test conditions	Min Typ. Max	Units
Operating voltage Test voltage Partial discharge extinction volt. Creep path input-output Creep path output-output Maximum dV/dt at dV=1000 V	Continuous or repeated ( 50 Hz/1 min (Note 11) IEC270 (Note 12) Note 13	Note 4) 1200 4000 >1700 20 25 100	V <sub>dc</sub> V <sub>AC(eff)</sub> V <sub>AC(pk)</sub> mm mm kV/µs
Collector current	Remarks	Min Typ. Max	Units
Max. IGBT collector current	Note 14	1400	А

All data refer to +25°C and  $V_{DC}$  = 15 V unless otherwise specified

Footnotes to the key data

- 1) The drivers have a zener diode on each channel for over-voltage protection. When the feed voltage exceeds 16V, this protection may be exposed to thermal overload.
- 2) If the specified power consumption is exceeded, this indicates an overload of the DC/DC converter. It should be noted that these DC/DC converters are not protected against overload.
- 3) Application-specific self-heating of gate drivers and IGBT modules, especially at high switching frequency, must be taken into account. As a rule, the switching frequency is limited due to the switching losses of the IGBT modules. Because CONCEPT cannot predict how the drivers will be incorporated in the user's application, no binding recommended value for self-heating and thus for the maximum useable output power can be made. Users are therefore recommended to check the gate driver's ambient temperature within the system.
- 4) This limit is due to active clamping. Refer to the "Description and Application Manual for 2SB315A SCALE Dual-Channel Plug-and-play IGBT Driver".
- 5) Under-voltage monitoring of the supply voltage to the gate driver. If the voltage drops below this limit, the power modules are switched off.
- 6) The gate current is limited by the gate resistors located on the driver.
- 7) Pulse width of the direct output of the gate drive unit (excluding the delay of the gate resistors).
- 8) The typical blocking time after an error is 1 second. Versions with other blocking times may also be supplied if required.
- 9) Measured from the transition of the turn-on or turn-off command at the host controller to direct output of the gate drive unit (excluding the delay of the gate resistors).
- 10) Refers to the direct output of the gate drive unit (excluding the delay of the gate resistors).
- 11) The test voltage of 4000 V<sub>ac(rms)</sub>/50Hz may be applied only once during one minute. It should be noted that with this (strictly speaking obsolete) test method, some (minor) damage occurs to the insulation layers due to the partial discharge. Consequently, this test is not performed at CONCEPT as a series test. In the case of repeated insulation tests (e.g. module test, equipment test, system test), the subsequent tests should be performed with a lower test voltage: the test voltage is reduced by 400V for each additional test. The more modern if more elaborate partial-discharge measurement is preferable to such test methods as it is almost entirely non-destructive.
- 12) The partial discharge is not measured for the standard types. Tested and selected types with guaranteed partial-discharge immunity can be supplied for applications with maximum requirements and higher operating voltages (such as railroad applications).
- 13) This specification guarantees that the drive information will be transferred reliably even at a high DC-link voltage and with ultra-fast switching operations.



14) Due to the switching behaviour of the IGBT module and the response time of the IGBT driver the maximum collector current is limited to about 1400A at  $T_j = 150$ °C and  $U_{dc} = 1200$ V. At higher currents the desaturation protection of the driver will be activated at turn-on.

#### Important Notice

The data contained in this product data sheet is intended exclusively for technically trained staff. Handling all high-voltage equipment involves risk to life. Strict compliance with the respective safety regulations is mandatory!

Any handling of electronic devices is subject to the general specifications for protecting electrostatic-sensitive devices according to international standard IEC 747-1, Chapter IX or European standard EN 100015 (i.e. the workplace, tools, etc. must comply with these standards). Otherwise, this product may be damaged.

#### Legal Disclaimer

This data sheet specifies devices but cannot promise to deliver any specific characteristics. No warranty or guarantee is given – either expressly or implicitly – regarding delivery, performance or suitability.

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#### Technical Support

CONCEPT provides expert help for your questions and problems:

Internet: <u>www.IGBT-Driver.com/go/support</u>

## Quality

The obligation to high quality is one of the central features laid down in the mission statement of CT-Concept Technologie AG. The quality management system covers all stages of product development and production up to delivery. The drivers of the SCALE series are manufactured to the ISO 9001 standard.

## **Ordering Information**

The general terms and conditions of delivery of CT-Concept Technologie AG apply.

#### **Related IGBT**

**CONCEPT Driver Type #** 

Fuji 2MBI800VT-170E

2SB315A-2MBI800VT-170E

#### Information about Other Products

#### For drivers adapted to other high-voltage or high-power IGBT modules

Direct link: www.IGBT-Driver.com/go/plug-and-play

#### For other drivers and evaluation systems

Please click: www.IGBT-Driver.com

#### © Manufacturer

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